Jean Christophe Harmand

List of Publications by Year
in descending order

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191 papers	7,061 citations	47 h-index	78 g-index
		47006	66911
192 all docs	192 docs citations	192 times ranked	4384 citing authors

#	Article	IF	Citations
1	Inâ€Situ Transmission Electron Microscopy Observation of Germanium Growth on Freestanding Graphene: Unfolding Mechanism of 3D Crystal Growth During Van der Waals Epitaxy. Small, 2022, 18, e2101890.	10.0	5
2	Statistics of Nucleation and Growth of Single Monolayers in Nanowires: Towards a Deterministic Regime. Physica Status Solidi - Rapid Research Letters, 2022, 16, .	2.4	8
3	Regulated Dynamics with Two Monolayer Steps in Vaporâ€“Solidâ€“Solid Growth of Nanowires. ACS Nano, 2022, 16, 4397-4407.	14.6	5
4	Crystal polarity discrimination in GaN nanowires on graphene. Journal of Materials Chemistry C, 2021, 9, 9997-10004.	5.5	1
5	Quantitative Assessment of Carrier Density by Cathodoluminescence. I. GaAs Thin Films and Modeling. Physical Review Applied, 2021, 15, .	3.8	6
6	Quantitative Assessment of Carrier Density by Cathodoluminescence. II. GaAs Nanowires. Physical Review Applied, 2021, 15, .	3.8	4
7	Dynamics of Droplet Consumption in Vaporâ€“Liquidâ€“Solid IIIâ€“V Nanowire Growth. Crystal Growth and Design, 2021, 21, 4647-4655.	3.0	6
8	Investigation of the effect of the doping order in GaN nanowire pâ€“n junctions grown by molecular-beam epitaxy. Nanotechnology, 2021, 32, 085705.	2.6	7
9	DFT analysis of crystal polarity on graphene surface. Journal of Physics: Conference Series, 2021, 2015, 012105.	0.4	0
10	Selective Area Growth of GaN Nanowires on Graphene Nanodots. Crystal Growth and Design, 2020, 20, 552-559.	3.0	20
11	Nanoscale electrical analyses of axial-junction GaAsP nanowires for solar cell applications. Nanotechnology, 2020, 31, 145708.	2.6	14
12	Influence of surface passivation on the electrical properties of pâ€“iâ€“n GaAsP nanowires. Applied Physics Letters, 2020, 117, 123104.	3.3	4
13	Stable and high yield growth of GaP and In_{0.2}Ga_{0.8}As nanowire arrays using In as a catalyst. Nanoscale, 2020, 12, 18240-18248.	5.6	6
14	In Situ X-ray Diffraction Study of GaN Nucleation on Transferred Graphene. Crystal Growth and Design, 2020, 20, 4013-4019.	3.0	7
15	Phase Selection in Self-catalyzed GaAs Nanowires. Nano Letters, 2020, 20, 1669-1675.	9.1	83
16	GaN/Ga2O3 Core/Shell Nanowires Growth: Towards High Response Gas Sensors. Applied Sciences (Switzerland), 2019, 9, 3528.	2.5	13
17	Growth Dynamics of Gallium Nanodroplets Driven by Thermally Activated Surface Diffusion. Journal of Physical Chemistry Letters, 2019, 10, 5082-5089.	4.6	3
18	Importance of point defect reactions for the atomic-scale roughness of IIIâ€“V nanowire sidewalls. Nanotechnology, 2019, 30, 324002.	2.6	5

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19	Investigation of GaN nanowires containing AlN/GaN multiple quantum discs by EBIC and CL techniques. Nanotechnology, 2019, 30, 214006.	2.6	5
20	Morphology Tailoring and Growth Mechanism of Indium-Rich InGaN/GaN Axial Nanowire Heterostructures by Plasma-Assisted Molecular Beam Epitaxy. Crystal Growth and Design, 2018, 18, 2545-2554.	3.0	14
21	Measuring and Modeling the Growth Dynamics of Self-Catalyzed GaP Nanowire Arrays. Nano Letters, 2018, 18, 701-708.	9.1	55
22	Atomic Step Flow on a Nanofacet. Physical Review Letters, 2018, 121, 166101.	7.8	113
23	Energy harvesting efficiency in GaN nanowire-based nanogenerators: the critical influence of the Schottky nanocontact. Nanoscale, 2017, 9, 4610-4619.	5.6	29
24	Determination of n-Type Doping Level in Single GaAs Nanowires by Cathodoluminescence. Nano Letters, 2017, 17, 6667-6675.	9.1	35
25	In situpassivation of GaAsP nanowires. Nanotechnology, 2017, 28, 495707.	2.6	27
26	Shiba Bound States across the Mobility Edge in Doped InAs Nanowires. Physical Review Letters, 2017, 119, 097701.	7.8	8
27	Magnetic two-dimensional field effect transistor. Applied Physics Letters, 2017, 111, .	3.3	2
28	Class-A operation of an optically-pumped 16 Âµm-emitting quantum dash-based vertical-external-cavity surface-emitting laser on InP. Optics Express, 2017, 25, 11760.	3.4	6
29	Class-A Operation of InAs Quantum Dash-based Vertical-External-Cavity Surface-Emitting Laser. , 2017, , .		0
30	III-V Nanowires on Silicon: a possible route to Si-based tandem solar cells. , 2017, , .		0
31	Piezo-generator integrating a vertical array of GaN nanowires. Nanotechnology, 2016, 27, 325403.	2.6	50
32	Nitride Nanowires: From Rigid to Flexible Piezo-generators. Journal of Physics: Conference Series, 2016, 773, 012010.	0.4	1
33	Self-induced growth of vertical GaN nanowires on silica. Nanotechnology, 2016, 27, 135602.	2.6	33
34	Epitaxy of GaN Nanowires on Graphene. Nano Letters, 2016, 16, 4895-4902.	9.1	115
35	Electron beam induced current microscopy investigation of GaN nanowire arrays grown on Si substrates. Materials Science in Semiconductor Processing, 2016, 55, 72-78.	4.0	9
36	Sharpening the Interfaces of Axial Heterostructures in Self-Catalyzed AlGaAs Nanowires: Experiment and Theory. Nano Letters, 2016, 16, 1917-1924.	9.1	60

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37	Photon Cascade from a Single Crystal Phase Nanowire Quantum Dot. Nano Letters, 2016, 16, 1081-1085.	9.1	37
38	Voltage bistability of coherent electron injection and nonlinear dynamics of a Bloch oscillation in a semiconductor superlattice. Physical Review B, 2015, 91, .	3.2	3
39	Optical polarization properties of InAs/InP quantum dot and quantum rod nanowires. Nanotechnology, 2015, 26, 395701.	2.6	14
40	Abrupt GaP/GaAs Interfaces in Self-Catalyzed Nanowires. Nano Letters, 2015, 15, 6036-6041.	9.1	47
41	Crystallization of Si Templates of Controlled Shape, Size, and Orientation: Toward Micro- and Nanosubstrates. Crystal Growth and Design, 2015, 15, 2102-2109.	3.0	5
42	Modeling, synthesis and study of highly efficient solar cells based on III-nitride nanowire arrays grown on Si substrates. Journal of Physics: Conference Series, 2015, 643, 012115.	0.4	13
43	Class-A dual-frequency VECSEL at telecom wavelength. Optics Letters, 2014, 39, 5586.	3.3	27
44	Room-temperature optical manipulation of nuclear spin polarization in GaAsN. Physical Review B, 2014, 90, .	3.2	16
45	Random stacking sequences in III-V nanowires are correlated. Physical Review B, 2014, 89, .	3.2	13
46	Palladium assisted hetroepitaxial growth of an InAs nanowire by molecular beam epitaxy. Semiconductor Science and Technology, 2014, 29, 115005.	2.0	4
47	Recent advances in development of vertical-cavity based short pulse source at 1.55 Î¼m. Frontiers of Optoelectronics, 2014, 7, 1-19.	3.7	1
48	GaN nanowires for piezoelectric generators. Physica Status Solidi - Rapid Research Letters, 2014, 8, 414-419.	2.4	23
49	Design of III-V nanowires based micosources vertically coupled to a Si waveguide for optical interconnects. , 2014, , .		1
50	Impact of the GaN nanowire polarity on energy harvesting. Applied Physics Letters, 2014, 104, .	3.3	20
51	Record Pure Zincblende Phase in GaAs Nanowires down to 5 nm in Radius. Nano Letters, 2014, 14, 3938-3944.	9.1	82
52	Fabrication of an InGaAs spin filter by implantation of paramagnetic centers. Applied Physics Letters, 2013, 103, .	3.3	15
53	Bistability and nonlinear negative differential conductance in semiconductor superlattices illuminated by laser light. Applied Physics Letters, 2013, 103, 092106.	3.3	0
54	Photoreflectance, photoluminescence, and microphotoluminescence study of optical transitions between delocalized and localized states in GaN<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>0.02</mml:mn></mml:mrow></mml:msub></mml:math>As<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>0.98</mml:mn></mml:mrow></mml:msub></mml:math>, Ga<mml:math xmlns:m	3.2	49

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55	Phase coherent transport in GaAs/AlGaAs coreâ€“shellnanowires. Journal of Crystal Growth, 2013, 378, 546-548.	1.5	6
56	Growth of Vertical GaAs Nanowires on an Amorphous Substrate via a Fiber-Textured Si Platform. Nano Letters, 2013, 13, 2743-2747.	9.1	31
57	Improvement of the oxidation interface in an Al<scp>G</scp>a<scp>A</scp>s/<scp>A</scp>l_x<scp>O</scp>_y waveguide structure by using a Ga<scp>A</scp>s/<scp>A</scp>l<scp>A</scp>s superlattice. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 1171-1177.	1.8	0
58	Arsenic Pathways in Self-Catalyzed Growth of GaAs Nanowires. Crystal Growth and Design, 2013, 13, 91-96.	3.0	133
59	InP1â^'xAsx quantum dots in InP nanowires: A route for single photon emitters. Journal of Crystal Growth, 2013, 378, 519-523.	1.5	17
60	Predictive modeling of self-catalyzed III-V nanowire growth. Physical Review B, 2013, 88, .	3.2	158
61	Micro-Raman study of GaAs nanowires. , 2013, , .		0
62	Magnetic thaw-down and boil-off due to magneto acceptors in 2DEG. , 2013, , .		0
63	Conduction band structure in wurtzite GaAs nanowires: A resonant Raman scattering study. Applied Physics Letters, 2012, 100, .	3.3	30
64	Magnetic thaw down and boil-off of electrons in the quantum Hall effect regime due to magnetoacceptors in GaAs/GaAlAs heterostructures. Physical Review B, 2012, 86, .	3.2	6
65	Kinetics and Statistics of Vapor-Liquid-Solid Growth of III-V Nanowires. Materials Research Society Symposia Proceedings, 2012, 1408, 81.	0.1	0
66	Effect of diffusion from a lateral surface on the rate of GaN nanowire growth. Semiconductors, 2012, 46, 838-841.	0.5	11
67	N-Polar GaN Nanowires Seeded by Al Droplets on Si(111). Crystal Growth and Design, 2012, 12, 2724-2729.	3.0	54
68	Influence of shadow effect on the growth and shape of InAs nanowires. Journal of Applied Physics, 2012, 111, .	2.5	49
69	Cost-Effective Thermally-Managed 1.55-$mu{m m}$ VECSEL With Hybrid Mirror on Copper Substrate. IEEE Journal of Quantum Electronics, 2012, 48, 643-650.	1.9	15
70	Giant spin-dependent photo-conductivity in GaAsN dilute nitride semiconductor. Physical Review B, 2011, 83, .	3.2	18
71	Morphology of self-catalyzed GaN nanowires and chronology of their formation by molecular beam epitaxy. Nanotechnology, 2011, 22, 245606.	2.6	59
72	New Mode of Vaporâ^'Liquidâ^'Solid Nanowire Growth. Nano Letters, 2011, 11, 1247-1253.	9.1	132

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73	Subpicosecond pulse generation from a 156 â€‰Î¼m mode-locked VECSEL. Optics Letters, 2011, 36, 4377.	3.3	26
74	Dispersion management in a passively mode-locked VECSEL at 1.55 Î¼m. Proceedings of SPIE, 2011, , .	0.8	0
75	Carrier spin relaxation in GaInNAsSbâˆ•GaNAsSbâˆ•GaAs quantum well. , 2011, , .		0
76	GaP/GaAs1â^'xPx nanowires fabricated with modulated fluxes: A step towards the realization of superlattices in a single nanowire. Journal of Crystal Growth, 2011, 323, 293-296.	1.5	23
77	Quasi one-dimensional transport in single GaAs/AlGaAs core-shell nanowires. Applied Physics Letters, 2011, 98, .	3.3	22
78	Picosecond carrier lifetimes in dilute GaInNAs grown on InP substrate. Applied Physics Letters, 2011, 99, .	3.3	5
79	Effects of temperature on transition energies of GaAsSbN/GaAs single quantum wells. Journal of Physics Condensed Matter, 2011, 23, 325801.	1.8	2
80	Growth of III-Arsenide/Phosphide Nanowires by Molecular Beam Epitaxy. , 2011, , 68-88.		0
81	Growth of Inclined GaAs Nanowires by Molecular Beam Epitaxy: Theory and Experiment. Nanoscale Research Letters, 2010, 5, 1692-1697.	5.7	23
82	Effect of arsenic species on the kinetics of GaAs nanowires growth by molecular beam epitaxy. Journal of Crystal Growth, 2010, 312, 2073-2077.	1.5	27
83	Investigation of the electronic transport in GaN nanowires containing GaN/AlN quantum discs. Nanotechnology, 2010, 21, 425206.	2.6	31
84	Nucleation Antibunching in Catalyst-Assisted Nanowire Growth. Physical Review Letters, 2010, 104, 135501.	7.8	100
85	Room temperature picosecond mode-locked pulse generation from a 1.55µm VECSEL with an InGaAsN/GaAsN fast saturable absorber mirror. , 2010, , .		0
86	Growth kinetics of a single<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mtext>InP</mml:mtext><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</ Physical Review B, 2010, 81, .	3.2	88
87	Effect of nitrogen on the GaAs0.9â^'xNxSb0.1 dielectric function from the near-infrared to the ultraviolet. Applied Physics Letters, 2010, 97, 201903.	3.3	17
88	Silicon nanowires: Diameter dependence of growth rate and delay in growth. Applied Physics Letters, 2010, 96, .	3.3	64
89	Local structure of indium in quinary (InGa)(AsSbN)/GaAs quantum wells. Physical Review B, 2010, 82, .	3.2	3
90	Crystal Phase Quantum Dots. Nano Letters, 2010, 10, 1198-1201.	9.1	233

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91	Growth, structure and phase transitions of epitaxial nanowires of III-V semiconductors. Journal of Physics: Conference Series, 2010, 209, 012002.	0.4	14
92	Wide InP Nanowires with Wurtzite/Zincblende Superlattice Segments Are Type-II whereas Narrower Nanowires Become Type-I: An Atomistic Pseudopotential Calculation. Nano Letters, 2010, 10, 4055-4060.	9.1	76
93	Ultrashort pulse generation from 156 Âµm mode-locked VECSEL at room temperature. Optics Express, 2010, 18, 19902.	3.4	16
94	Nanowires for quantum optics. , 2010, , .		1
95	Effects of repulsive and attractive ionized impurities on the resistivity of semiconductor heterostructures in the quantum Hall regime. Physical Review B, 2009, 80, .	3.2	7
96	Spin-dependent photoconductivity in nonmagnetic semiconductors at room temperature. Applied Physics Letters, 2009, 95, .	3.3	21
97	Epitaxial growth and picosecond carrier dynamics of GaInAs/GaInNAs superlattices. Applied Physics Letters, 2009, 95, 141910.	3.3	6
98	Wurtzite GaAs/AlGaAs coreâ€“shell nanowires grown by molecular beam epitaxy. Nanotechnology, 2009, 20, 415701.	2.6	34
99	Si Incorporation in InP Nanowires Grown by Au-Assisted Molecular Beam Epitaxy. Journal of Nanomaterials, 2009, 2009, 1-7.	2.7	11
100	Electron spin control in dilute nitride semiconductors. Journal of Physics Condensed Matter, 2009, 21, 174211.	1.8	14
101	Semiconductor quantum-wires and nano-wires for optoelectronic applications. Journal of Materials Science: Materials in Electronics, 2009, 20, 94-101.	2.2	8
102	Vibrational spectroscopies: a natural â€œmesoscopeâ€•for the study of spontaneous ordering in alloys. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1303-1306.	0.8	0
103	Room-temperature defect-engineered spin filter based on a non-magnetic semiconductor. Nature Materials, 2009, 8, 198-202.	27.5	94
104	Growth and structural characterization of GaAs/GaAsSb axial heterostructured nanowires. Journal of Crystal Growth, 2009, 311, 1847-1850.	1.5	23
105	Critical diameters and temperature domains for MBE growth of IIIâ€“V nanowires on lattice mismatched substrates. Physica Status Solidi - Rapid Research Letters, 2009, 3, 112-114.	2.4	116
106	Towards a monolithic optical cavity for atom detection and manipulation. European Physical Journal D, 2009, 53, 107-111.	1.3	4
107	Role of nonlinear effects in nanowire growth and crystal phase. Physical Review B, 2009, 80, .	3.2	90
108	Potential of semiconductor nanowires for single photon sources. Proceedings of SPIE, 2009, , .	0.8	4

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109	Photoluminescence study of nitrogen effects on confined states in GaAs_{1â^'x}N_xGaAs quantum wells. EPJ Applied Physics, 2009, 47, 30302.	0.7	6
110	Thermal optimization of 1.55ÂÎ¼m OP-VECSEL with hybrid metalâ€“metamorphic mirror for single-mode high power operation. Optical and Quantum Electronics, 2008, 40, 155-165.	3.3	43
111	Optical constants and critical-point parameters of GaAs1-xSbxalloy films grown on GaAs. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 833-836.	1.8	2
112	Growth kinetics and crystal structure of semiconductor nanowires. Physical Review B, 2008, 78, .	3.2	276
113	Shape modification of III-V nanowires: The role of nucleation on sidewalls. Physical Review E, 2008, 77, 031606.	2.1	59
114	Femtosecond pulse generation around 1500nm using a GaInNAsSb SESAM. Optics Express, 2008, 16, 18739.	3.4	10
115	Facet and in-plane crystallographic orientations of GaN nanowires grown on Si(111). Nanotechnology, 2008, 19, 155704.	2.6	82
116	Wurtzite to Zinc Blende Phase Transition in GaAs Nanowires Induced by Epitaxial Burying. Nano Letters, 2008, 8, 1638-1643.	9.1	63
117	Zinc blende GaAsSb nanowires grown by molecular beam epitaxy. Nanotechnology, 2008, 19, 275605.	2.6	53
118	Competition between confinement potential fluctuations and band-gap renormalization effects in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>In</mml:mtext></mml:mrow><mml:mrow><mml:mn>0.53</mml:mn></mml:mrow></mml:msub></mml:mrow></mml:math>Ga<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>As</mml:mtext></mml:mrow><mml:mrow><mml:mn>0.47</mml:mn></mml:mrow></mml:msub></mml:mrow></mml:math>/InP single quantum wells. Physical Review B, 2008, 77, .	3.2	9
119	Strain effects of InP/Si and InP/porous Si studied by spectroscopic ellipsometry. EPJ Applied Physics, 2008, 42, 99-102.	0.7	0
120	Photoluminescence properties of a Si doped InGaAs/InGaAlAs superlattice. Journal of Physics Condensed Matter, 2007, 19, 086207.	1.8	5
121	Combined Raman study of InGaAsN from the N-impurity and InGaAs-matrix sides. Applied Physics Letters, 2007, 91, 051910.	3.3	4
122	Au-assisted molecular beam epitaxy of InAs nanowires: Growth and theoretical analysis. Journal of Applied Physics, 2007, 102, 094313.	2.5	136
123	Growth of GaN free-standing nanowires by plasma-assisted molecular beam epitaxy: structural and optical characterization. Nanotechnology, 2007, 18, 385306.	2.6	109
124	Why Does Wurtzite Form in Nanowires of III-V Zinc Blende Semiconductors?. Physical Review Letters, 2007, 99, 146101.	7.8	669
125	Growth and Characterization of InP Nanowires with InAsP Insertions. Nano Letters, 2007, 7, 1500-1504.	9.1	110
126	Redistribution of nitrogen localized states in GaAsN layer doped Silicon. EPJ Applied Physics, 2007, 38, 221-225.	0.7	0

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127	Diffusion-controlled growth of semiconductor nanowires: Vapor pressure versus high vacuum deposition. Surface Science, 2007, 601, 4395-4401.	1.9	57
128	Large intrinsic birefringence in zinc-blende based artificial semiconductors. Comptes Rendus Physique, 2007, 8, 1174-1183.	0.9	1
129	Effect of deposition conditions on nanowhisker morphology. Semiconductors, 2007, 41, 865-874.	0.5	5
130	Nucleation at the lateral surface and the shape of whisker nanocrystals. Semiconductors, 2007, 41, 1240-1247.	0.5	2
131	Quantum-well saturable absorber at 1.55Î¼m on GaAs substrate with a fast recombination rate. Applied Physics Letters, 2006, 88, 201110.	3.3	36
132	Temperature conditions for GaAs nanowire formation by Au-assisted molecular beam epitaxy. Nanotechnology, 2006, 17, 4025-4030.	2.6	107
133	Theoretical analysis of the vapor-liquid-solid mechanism of nanowire growth during molecular beam epitaxy. Physical Review E, 2006, 73, 021603.	2.1	163
134	The effect of potential fluctuations on the optical properties of InGaAsâˆ•InGaAlAs single and coupled double quantum wells. Journal of Applied Physics, 2006, 100, 053519.	2.5	10
135	Clustering in GaAsSbN alloys as a possible origin of their atypical optical behavior: a Sb K-edge X-ray absorption study. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1931-1934.	0.8	7
136	The role of surface diffusion of adatoms in the formation of nanowire crystals. Semiconductors, 2006, 40, 1075-1082.	0.5	48
137	Optimization and Characterization of InGaAsN/GaAs Quantum-well Ridge Laser Diodes for High Frequency Operation. Optical and Quantum Electronics, 2006, 38, 313-324.	3.3	9
138	Calculation of the temperature profile in nanowhiskers growing on a hot substrate. Physical Review B, 2006, 73, .	3.2	32
139	Scaling of the saturation energy in microcavity saturable absorber devices. Applied Physics Letters, 2006, 88, 153513.	3.3	15
140	Continuous wave and time resolved spectroscopy of InAsN/GaAsN based quantum dots. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 2598-2603.	1.8	3
141	MBE growth of InAsN on (100) InAs substrates. Physica Status Solidi (B): Basic Research, 2005, 242, R43-R45.	1.5	18
142	The Free Exciton Binding Energy in a Strained GaN0.02As0.98 Layer. AIP Conference Proceedings, 2005, , .	0.4	5
143	Spin dynamics in dilute nitride semiconductors at room temperature. Applied Physics Letters, 2005, 87, 252115.	3.3	43
144	The effect of potential fluctuations on the optical properties of InGaAsâˆ•InAlAs superlattices. Journal of Applied Physics, 2005, 97, 103518.	2.5	19

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145	Floor free 10-Gb/s transmission with directly modulated GaInNAs-GaAs 1.35-/spl mu/m laser for metropolitan applications. IEEE Photonics Technology Letters, 2005, 17, 971-973.	2.5	19
146	Analysis of vapor-liquid-solid mechanism in Au-assisted GaAs nanowire growth. Applied Physics Letters, 2005, 87, 203101.	3.3	249
147	GaInAs/GaAs quantum-well growth assisted by Sb surfactant: Toward 1.3â€‚Î¼m emission. Applied Physics Letters, 2004, 84, 3981-3983.	3.3	81
148	Photoreflectance investigations of the energy level structure in GaInNAs-based quantum wells. Journal of Physics Condensed Matter, 2004, 16, S3071-S3094.	1.8	50
149	Photoreflectance investigations of oscillator strength and broadening of optical transitions for GaAsSbâ€“GaInAs/GaAs bilayer quantum wells. Applied Physics Letters, 2004, 84, 3453-3455.	3.3	36
150	Ultrafast InGaAs/InGaAlAs multiple-quantum-well electro-absorption modulator for wavelength conversion at high bit rates. Applied Physics Letters, 2004, 84, 4268-4270.	3.3	15
151	Experimental investigation of the CMN matrix element in the band anticrossing model for GaAsN and GaInAsN layers. Solid State Communications, 2004, 129, 353-357.	1.9	30
152	Photoluminescence characteristics of GaAsSbN/GaAs epilayers lattice-matched to GaAs substrates. Solid State Communications, 2004, 132, 707-711.	1.9	37
153	Morphology and composition of highly strained InGaAs and InGaAsN layers grown on GaAs substrate. Applied Physics Letters, 2004, 84, 203-205.	3.3	49
154	Band structure calculations for dilute nitride quantum wells under compressive or tensile strain. Journal of Physics Condensed Matter, 2004, 16, S3215-S3227.	1.8	14
155	Investigation of recombination processes involving defect-related states in (Ga,In)(As,Sb,N) compounds. EPJ Applied Physics, 2004, 27, 313-316.	0.7	29
156	Low switching energy saturable absorber device for 40Gbit/s networks. , 2004, , .		2
157	Role of nitrogen in the mobility drop of electrons in modulation-doped GaAsN/AlGaAs heterostructures. Solid State Communications, 2003, 126, 333-337.	1.9	49
158	Doping dependence of millimeterwave negative differential conductance in strain-compensated GaInAs/AlInAs superlattices. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 294-296.	2.7	3
159	Effect of temperature on the optical properties of GaAsSbN/GaAs single quantum wells grown by molecular-beam epitaxy. Journal of Applied Physics, 2003, 93, 4475-4479.	2.5	52
160	Influence of carrier localization on modulation mechanism in photoreflectance of GaAsN and GaInAsN. Applied Physics Letters, 2003, 83, 1379-1381.	3.3	35
161	Investigations on GaInNAsSb quinary alloy for 1.5 Î¼m laser emission on GaAs. Applied Physics Letters, 2003, 83, 1298-1300.	3.3	50
162	Photoluminescence study of interfaces between heavily doped Al0.48In0.52As:Si layers and InP (Fe) substrates. Journal of Applied Physics, 2002, 91, 8999-9004.	2.5	10

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163	Effect of nitrogen and temperature on the electronic band structure of GaAs1â^'xNx alloys. Applied Physics Letters, 2002, 80, 2075-2077.	3.3	40
164	GaNAsSb: how does it compare with other dilute IIIÂV-nitride alloys?. Semiconductor Science and Technology, 2002, 17, 778-784.	2.0	93
165	Effect of nitrogen in the electronic structure of GaAsN and GaAsSb(N) compounds. Materials Science and Engineering C, 2002, 21, 251-254.	7.3	26
166	Temperature-dependent valence band offset and band-gap energies of pseudomorphic GaAsSb on GaAs. Journal of Applied Physics, 2001, 89, 5473-5477.	2.5	112
167	Comparison of light- and heavy-ion-irradiated quantum-wells for use as ultrafast saturable absorbers. Applied Physics Letters, 2001, 79, 2722-2724.	3.3	34
168	Ultrafast saturable absorption at 1.55 Î¼m in heavy-ion-irradiated quantum-well vertical cavity. Applied Physics Letters, 2000, 76, 1371-1373.	3.3	33
169	Comparison of nitrogen incorporation in molecular-beam epitaxy of GaAsN, GaInAsN, and GaAsSbN. Applied Physics Letters, 2000, 77, 2482-2484.	3.3	106
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